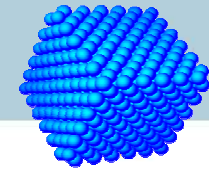
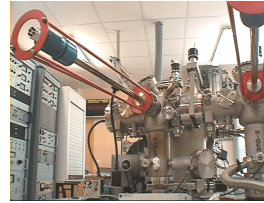
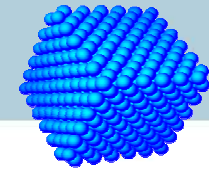


# Simulation des propriétés mécaniques, piezoélectriques, électroniques ou optiques de nanostructures à semiconducteurs

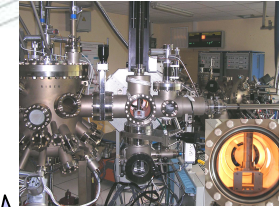
**J. Even**



- I. Introduction**
- II. Utilisation de fonctions mathématiques spéciales**
- III. Approximation axiale pour les îlots**
- IV. Potentiel piezoélectrique**
- V. Etats électroniques**
- VI. Effets excitoniques**
- VII. Conclusion**

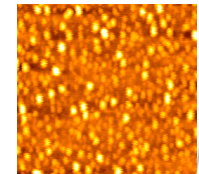
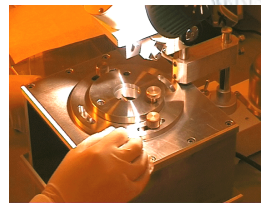


**Croissance de nanostructures (EJM)**



**Composants optoélectroniques**

**Salle blanche, Caractérisations des composants**

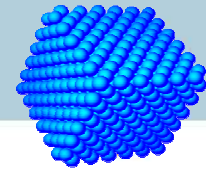


**Caractérisations optiques et structurales des matériaux**

**AFM, RX, PL, Pompe-sonde...**

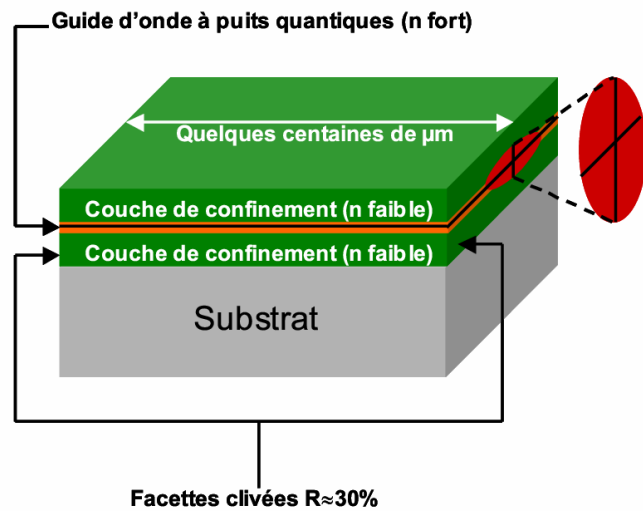


## Exemple : laser pour telecoms optiques



### Laser à cavité horizontale

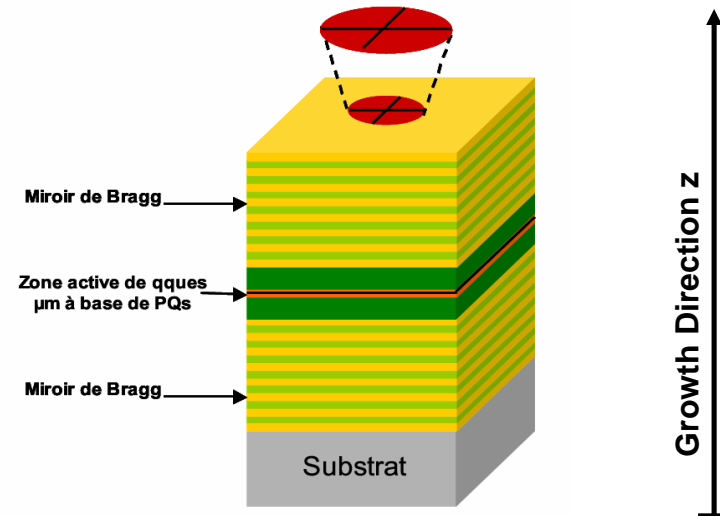
Longue distance



- $\lambda = 1,55 \mu\text{m}$
- Débit (2.5, 10 et 40 Gbits/sec avec modulation externe)
- Besoin limité en composants
  - ↳ Composant complexe et cher

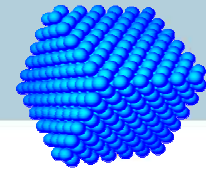
### Laser à cavité verticale (VCSEL)

Courte distance

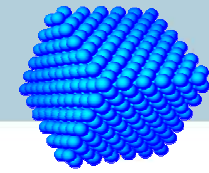


- (MAN / LAN)  $\lambda = 1,3 \text{ et } 1,55 \mu\text{m}$  - (DATAcom)  $\lambda = 0,85 \mu\text{m}$
- Débit (jusqu'à 10 Gbits/sec en modulation directe)
- Besoin important en composants
  - ↳ Fabrication à grande échelle et cout faible

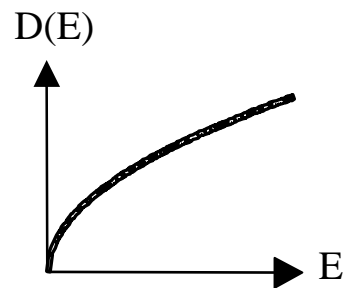
## Plusieurs échelles



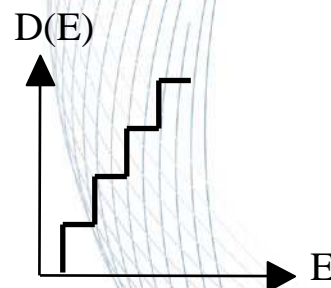
- échelle nano : effets quantiques et anisotropie des nanostructures à semiconducteurs
- échelle micro : effets de confinement optique, d'anisotropie, de cross-talk électronique des zones actives et cavités
- échelle méso (cm) : effets électrique (contacts) et thermique (évacuation de la chaleur, cross-talk) pour les composants
- échelle macro : insertion du composant dans un système (taux d'erreurs, pertes d'insertion ...)



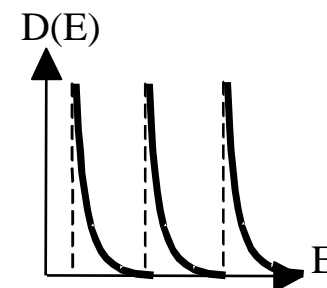
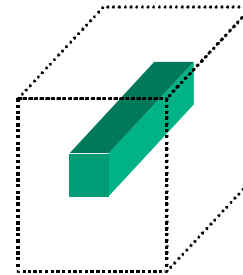
**Massif**  
**3D**



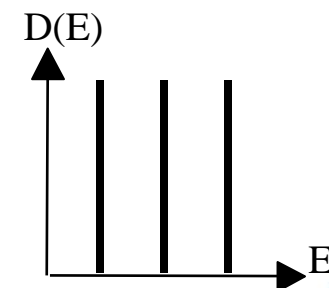
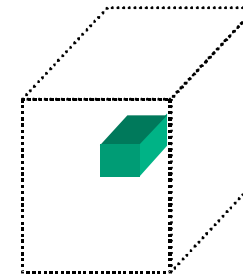
**Puits**  
**2D**



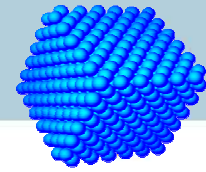
**Fils**  
**1D**



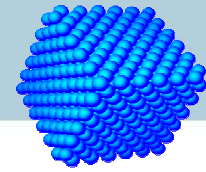
**Ilot**  
**0D**



**Densité d'états électroniques**



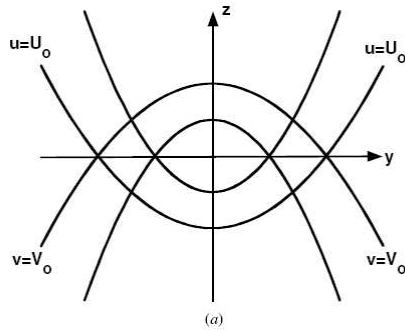
- I. Introduction
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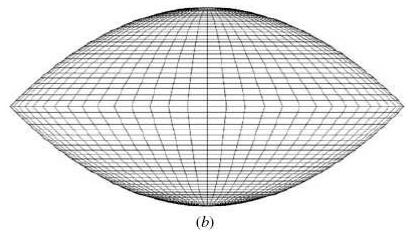
$$x = auv \cos(\theta) \quad y = auv \sin(\theta) \quad z = a(u^2 - v^2)/2.$$

$$(u, v, \theta) (0 \leq u \leq \infty, 0 \leq v \leq \infty \text{ and } 0 \leq \theta \leq 2\pi)$$

**Plots quantiques lenticulaires en régime de confinement fort**



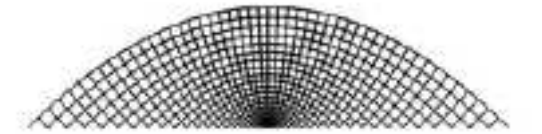
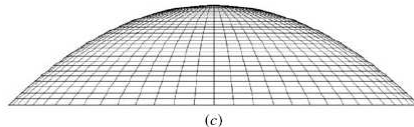
$$H = \frac{-\hbar^2}{2} \vec{\nabla} \frac{1}{m(\vec{r})} \vec{\nabla} + V(\vec{r}) = -\frac{\hbar^2}{2a^2(u^2 + v^2)} \left[ \frac{1}{u} \frac{\partial}{\partial u} \frac{u}{m(u,v)} \frac{\partial}{\partial u} + \frac{\partial}{\partial v} \frac{v}{m(u,v)} \frac{\partial}{\partial v} \right] - \frac{\hbar^2}{2a^2 u^2 v^2 m(u,v)} \frac{\partial^2}{\partial \theta^2} + V(u, v).$$



$$\Psi(u, v, \theta) = f(u)g(v) e^{int}$$

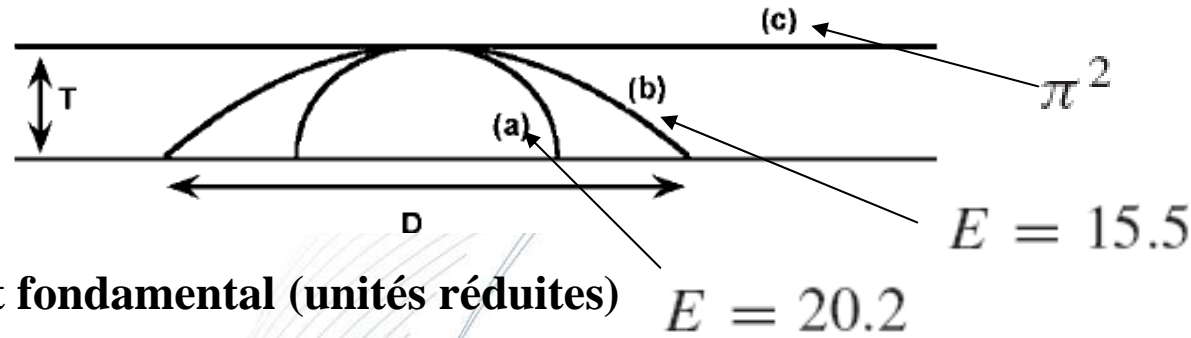
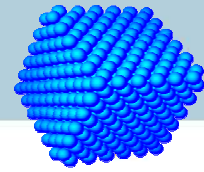
$$u^2 \frac{d^2 f}{du^2} + u \frac{df}{du} + (Eu^4 - Cu^2 - n^2) f = 0$$

$$v^2 \frac{d^2 g}{dv^2} + v \frac{dg}{dv} + (Ev^4 + Cv^2 - n^2) g = 0$$

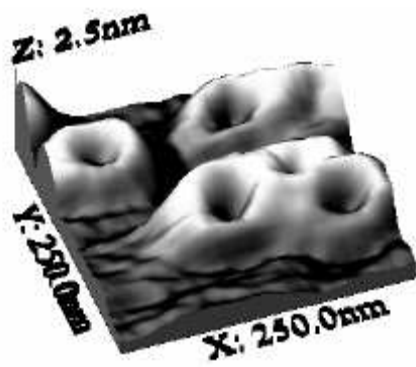


$$f(u) = NF(u, C, E, n) = N e^{-i\sqrt{E}u^2/2} (i\sqrt{E}u^2)^{n/2} \phi \left( \frac{-iC}{4\sqrt{E}} + \frac{n+1}{2}, n+1, i\sqrt{E}u^2 \right)$$

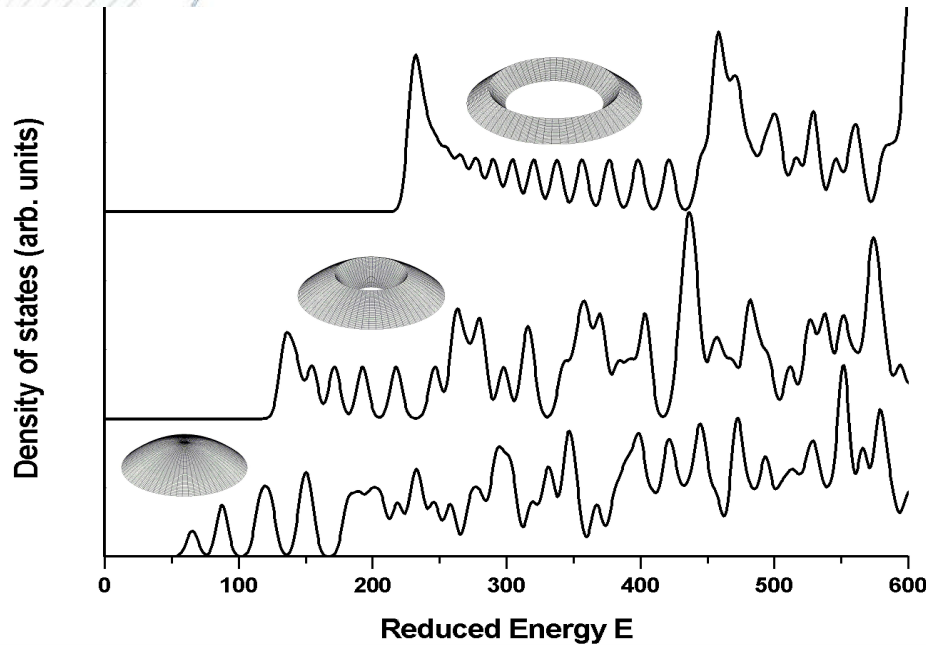




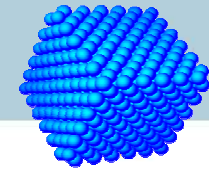
Energie de l'état fondamental (unités réduites)



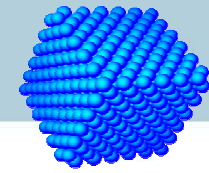
Anneaux quantiques



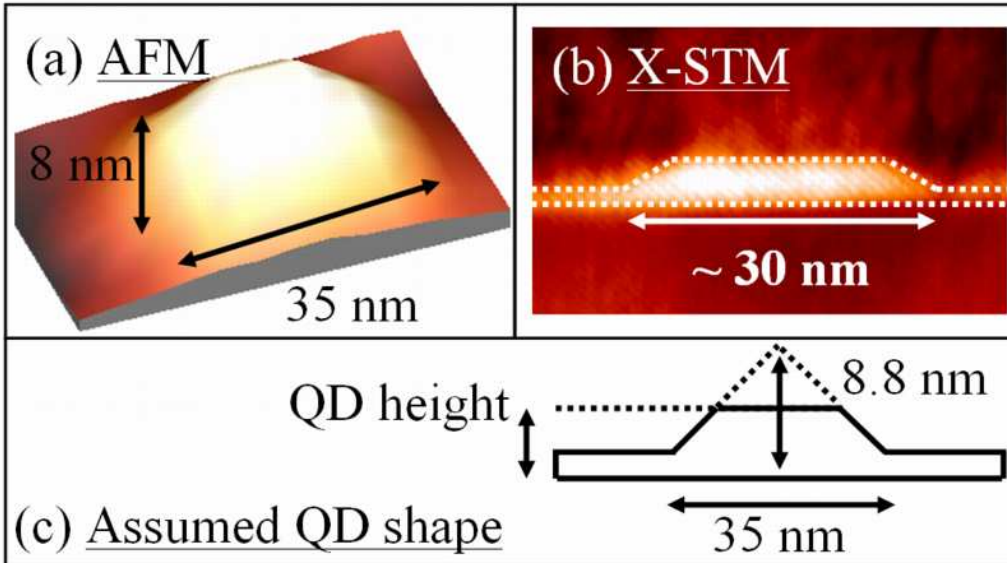
$$f(u) = F(u, C, E, m) = e^{-i\sqrt{E}u^2/2} (i\sqrt{E}u^2)^{m/2} \begin{pmatrix} \lambda_f \phi \left( \frac{-iC}{4\sqrt{E}} + \frac{m+1}{2}, m+1, i\sqrt{E}u^2 \right) \\ + \mu_f \psi \left( \frac{-iC}{4\sqrt{E}} + \frac{m+1}{2}, m+1, i\sqrt{E}u^2 \right) \end{pmatrix}$$



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# Îlots InAs/InP sur substrat (100) ou (311)

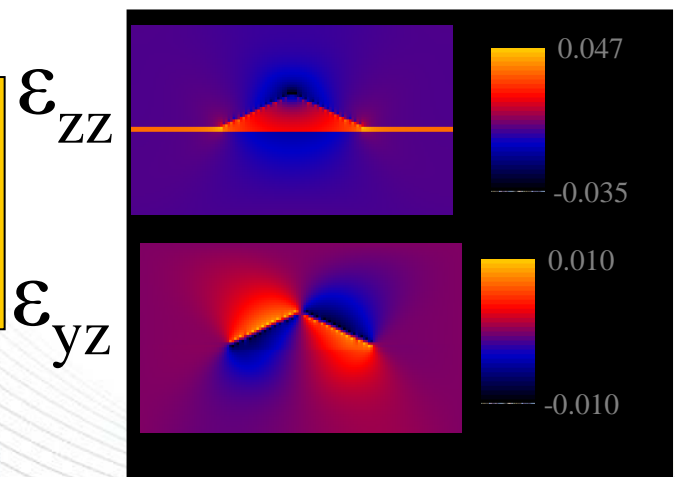


Cornet (*Phys. Rev. B* 2006) :  
simulation 3D pour InP(311) ou InP(100)  
(supercomputer Berlin TUB)



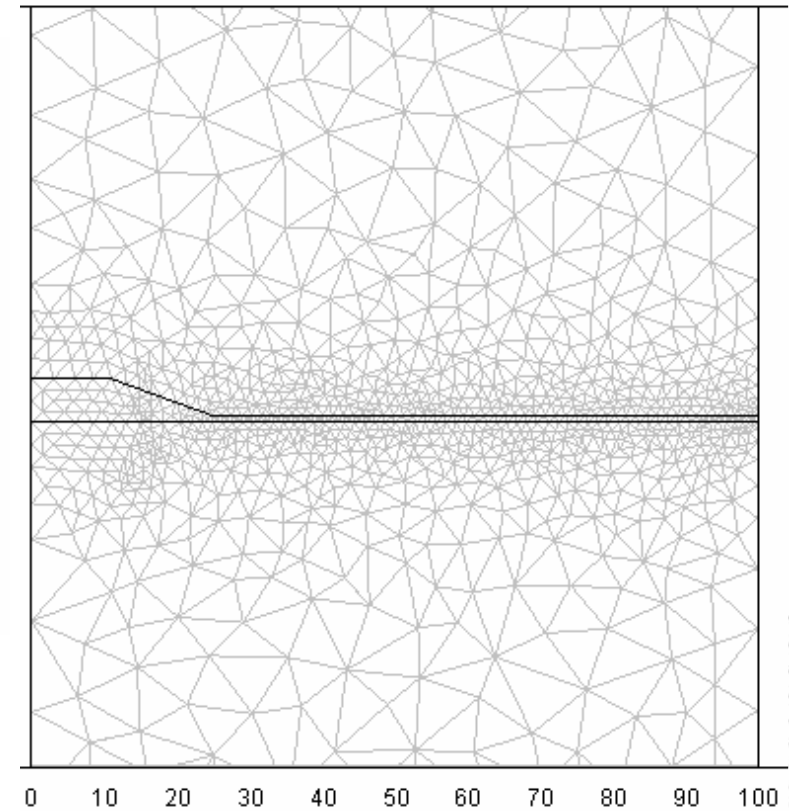
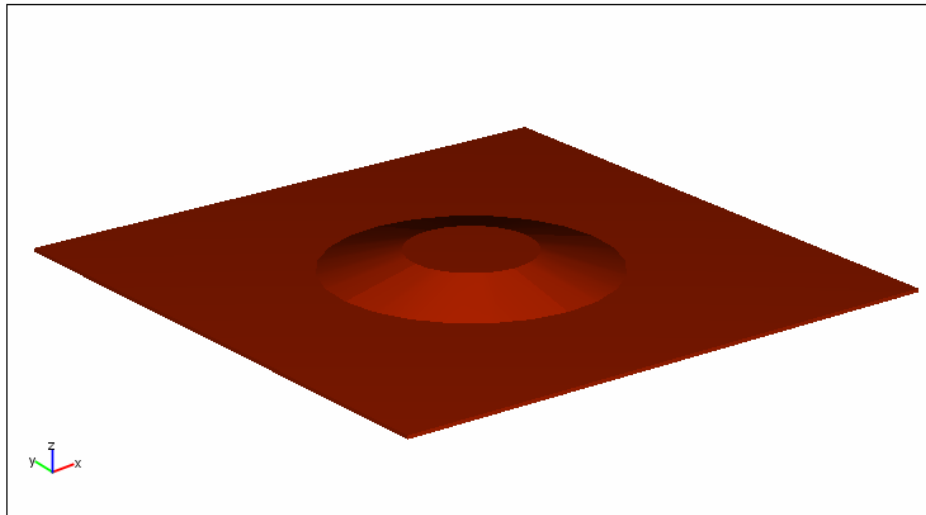
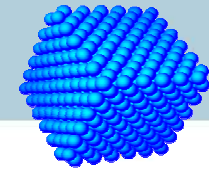
• **Symétrie Axiale  $C_{\infty v}$**  pour la géométrie sur substrat (100)

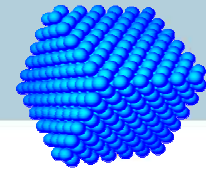
➤ **Les contraintes internes aux îlots sont associées au désaccord de maille entre InAs (îlot) et InP (substrat et barrière)**



• “hydrostatic” component

• “shear” component





Description en coordonnées cylindriques :  $r, \phi, z \longrightarrow \epsilon_{rr}, \epsilon_{\phi\phi}, \epsilon_{zz}, \epsilon_{rz}$

approximation  
 “transverse isotrope”  
 pour les matériaux  
 cubiques en maille  
 zinc-blende

$$\begin{pmatrix}
 C'_{11} & C'_{12} & C_{12} & 0 & 0 & 0 \\
 C'_{12} & C'_{11} & C_{12} & 0 & 0 & 0 \\
 C_{12} & C_{12} & C'_{11} & 0 & 0 & 0 \\
 0 & 0 & 0 & C_{44} & 0 & 0 \\
 0 & 0 & 0 & 0 & C_{44} & 0 \\
 0 & 0 & 0 & 0 & 0 & \bar{C}
 \end{pmatrix}$$

$$C'_{11} = \frac{C_{11} + C_{12}}{2} + \bar{C}$$

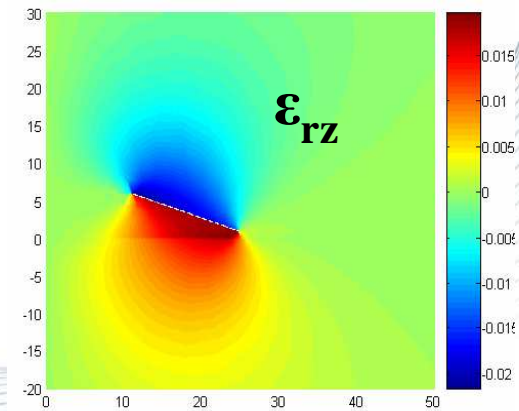
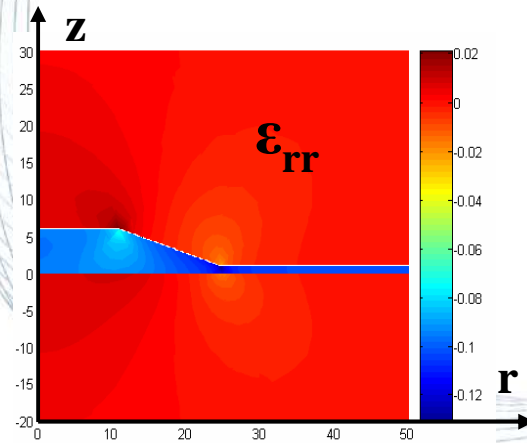
$$C'_{12} = \frac{C_{11} + C_{12}}{2} - \bar{C}$$

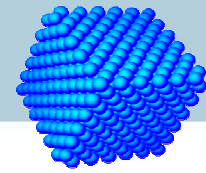
4 paramètres

retour en  
 coordonnées  
 cartésiennes

$$\begin{aligned}
 \epsilon_{xx} &= \cos^2(\varphi)\epsilon_{rr} + \sin^2(\varphi)\epsilon_{\phi\phi} & \epsilon_{xz} &= \cos(\varphi)\epsilon_{rz} & \epsilon_{xy} &= \frac{\sin(2\varphi)}{2}(\epsilon_{rr} - \epsilon_{\phi\phi}) \\
 \epsilon_{yy} &= \sin^2(\varphi)\epsilon_{rr} + \cos^2(\varphi)\epsilon_{\phi\phi} & \epsilon_{yz} &= \sin(\varphi)\epsilon_{rz}
 \end{aligned}$$

Exemple : InAs/GaP



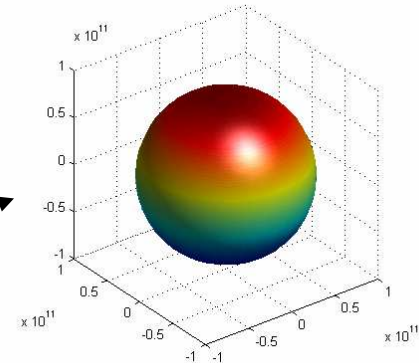
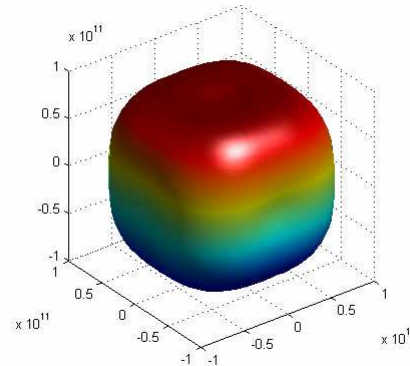


## "band warping" des phonons acoustiques

test : → vitesses du son dans InAs

Isosurfaces des vitesses longitudinales

Zinc blende

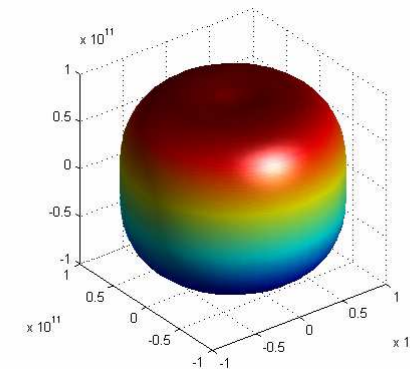
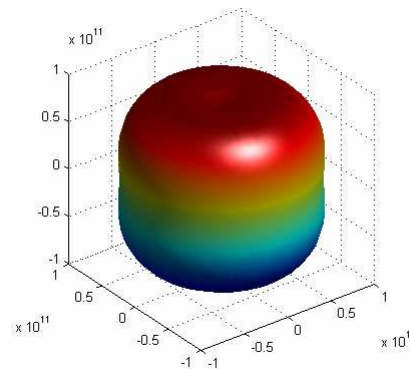
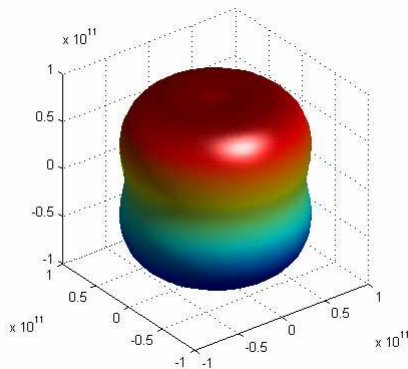


"isotrope 3D"

$d = 0$

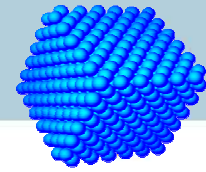
$d = 0.5$

$d = 1$

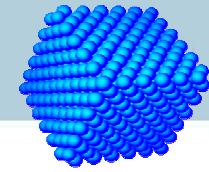


Approx. "transverse isotrope"

$$\bar{C} = \frac{C_{11} - C_{12}}{2} + \left( C_{44} - \frac{C_{11} - C_{12}}{2} \right) d$$



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## Potentiel piezoélectrique : potentiel électrique associé aux déformations dans l'îlot et dans le substrat

### 1<sup>er</sup> ordre : calcul semi-analytique (axial 2D Femlab)

$$\bar{P}_1 = 2e_{14} \left[ \sin(2\varphi)\epsilon_{rz}\bar{u}_r + \cos(2\varphi)\epsilon_{rz}\bar{u}_\varphi + \frac{\sin(2\varphi)}{2}(\epsilon_{rr} - \epsilon_{\varphi\varphi})\bar{u}_z \right] \longrightarrow V_1(r, \varphi, z) = \sin(2\varphi)f_1(r, z)$$

J. Even, Appl. Phys. Lett. (2007)

### 2<sup>ème</sup> ordre calcul semi-analytique (axial 2D Femlab)

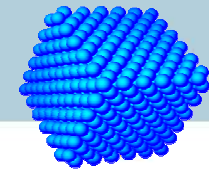
G. Bester, Phys. Rev. Lett. (2006)

### *Calcul Ab initio* (abinit) des constantes piezoélectriques quadratiques :

$$\text{InAs} \quad B_{114} = -0.531\text{Cm}^{-2} \quad B_{124} = -4.076\text{Cm}^{-2} \quad B_{156} = -0.120\text{Cm}^{-2}$$

$$\bar{P}_2 = \left[ \begin{aligned} &\frac{\sin(2\varphi)}{2} \left[ 2B_{114}(\epsilon_{rr} + \epsilon_{\varphi\varphi})\epsilon_{rz} + 2B_{124}(\epsilon_{rr} + \epsilon_{\varphi\varphi} + 2\epsilon_{zz})\epsilon_{rz} + 4B_{156}(\epsilon_{rr} - \epsilon_{\varphi\varphi})\epsilon_{rz} \right] \bar{u}_r \\ &+ \cos(2\varphi) \left[ 2B_{114}\epsilon_{\varphi\varphi}\epsilon_{rz} + 2B_{124}(\epsilon_{rr} + \epsilon_{zz})\epsilon_{rz} \right] \bar{u}_\varphi \\ &+ \sin(2\varphi) \left[ B_{114}(\epsilon_{rr} - \epsilon_{\varphi\varphi})\epsilon_{zz} + B_{124}(\epsilon_{rr}^2 - \epsilon_{\varphi\varphi}^2) + 2B_{156}\epsilon_{rz}^2 \right] \bar{u}_z \end{aligned} \right] \longrightarrow V_2(r, \varphi, z) = \sin(2\varphi)f_2(r, z)$$





# Potentiel piezoélectrique (femlab)

2 variables

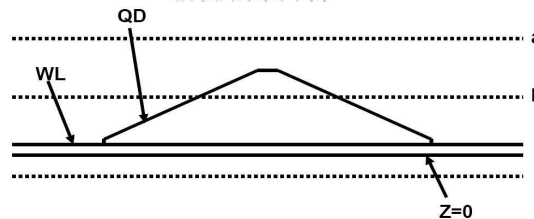
**Strains :**  
**Solver Manager - Solve For Axial Symmetry**  
**Solver Parameters : Stationary Linear**



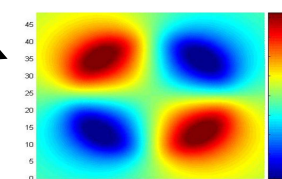
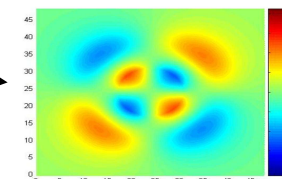
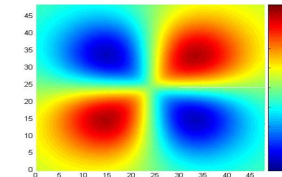
1 variable

**Poisson equation : piezoelectric potential**  
**Solver Manager - Solve For Coefficient form (c)**  
**Solver Manager : Initial Value Stored solution**  
**Solver Parameters : Stationary Linear**

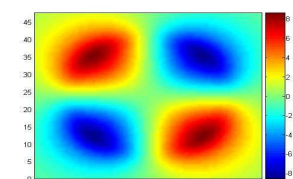
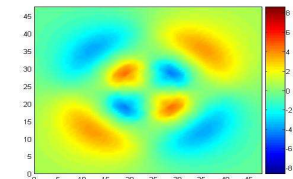
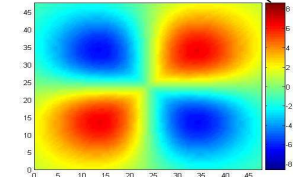
## Example : Cone InAs/InP



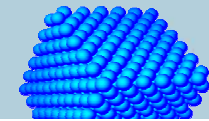
Femlab



TU Berlin (3D)

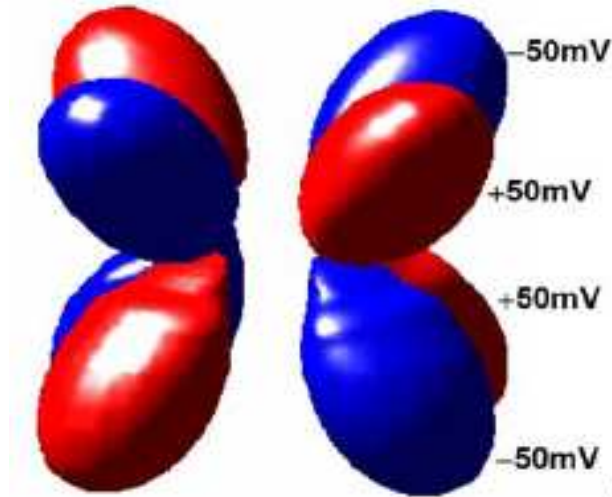


J. Even, Appl. Phys. Lett. (2007)

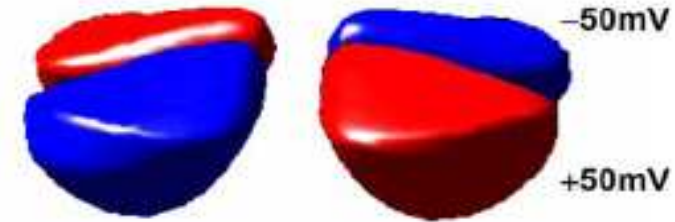


# Potentiel piezoélectrique

potentiel piezo  
Isosurfaces  
( $\pm 50$  mV)  
(Export de Femlab)

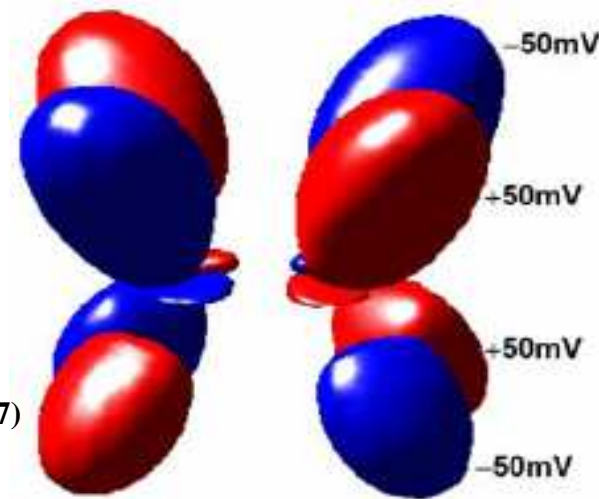


$P_1$  Linear (th.) component

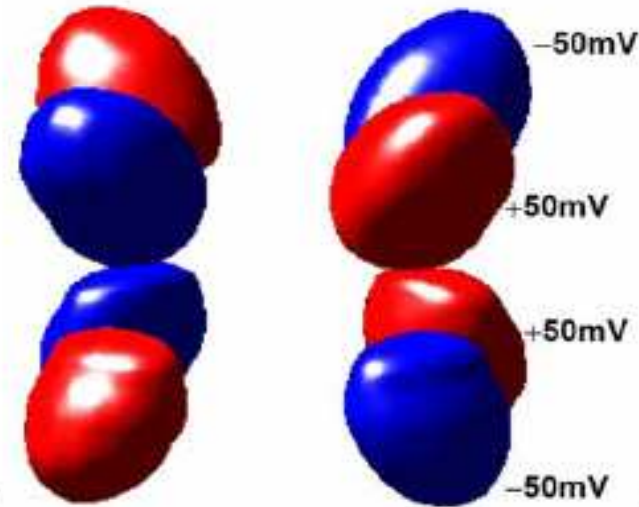


$P_2$  Quadratic (th.) component

InAs/GaP cone

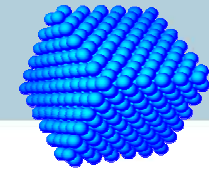


$P_1 + P_2$  (th.) component

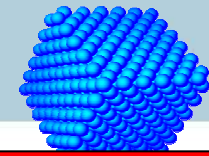


$P_1$  Linear (exp.) component

J. Even, Appl. Phys. Lett. (2007)



- I. Introduction
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- V. Etats électroniques**
- VI. Applications
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## Modèle k.p à 8 bandes

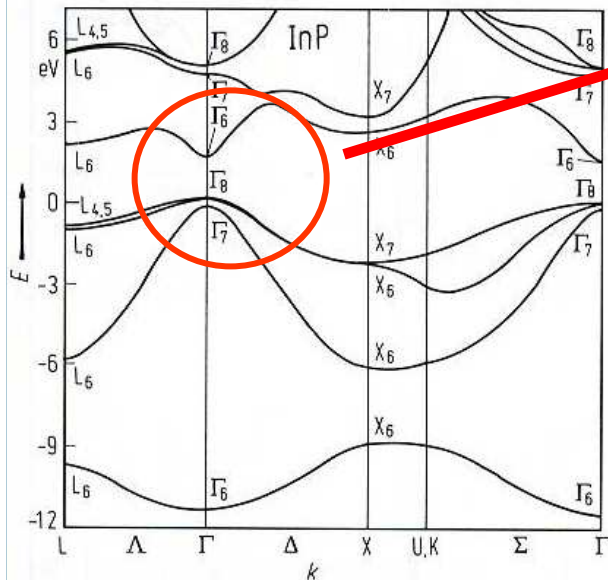
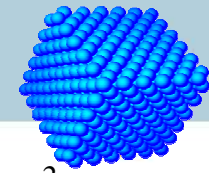


Fig. 1. InP. Band structure obtained with a non-local pseudopotential method [76C].

**Approximation k.p 8x8 :**

- Pour un matériau massif : 8 fonctions de Bloch
- Pour un îlot : 8 fonctions enveloppes associées

$$\begin{pmatrix}
 A & 0 & V^* & 0 & \sqrt{3}V & -\sqrt{2}U & -U & \sqrt{2}V^* \\
 0 & A & -\sqrt{2}U & -\sqrt{3}V^* & 0 & -V & \sqrt{2}V & U \\
 V & -\sqrt{2}U & -P+Q & -S^* & R & 0 & \sqrt{\frac{3}{2}}S & -\sqrt{2}Q \\
 0 & -\sqrt{3}V & -S & -P-Q & 0 & R & -\sqrt{2}R & \frac{1}{\sqrt{2}}S \\
 \sqrt{3}V^* & 0 & R^* & 0 & -P-Q & S^* & \frac{1}{\sqrt{2}}S^* & \sqrt{2}R^* \\
 -\sqrt{2}U & -V^* & 0 & R^* & S & -P+Q & \sqrt{2}Q & \sqrt{\frac{3}{2}}S^* \\
 -U & \sqrt{2}V^* & \sqrt{\frac{3}{2}}S^* & -\sqrt{2}R^* & \frac{1}{\sqrt{2}}S & \sqrt{2}Q & -P-\Delta & 0 \\
 \sqrt{2}V & U & -\sqrt{2}Q & \frac{1}{\sqrt{2}}S^* & \sqrt{2}R & \sqrt{\frac{3}{2}}S & 0 & -P-\Delta
 \end{pmatrix}$$



## Modèle k.p axial à 8 bandes

**Hamiltonien sans déformations :**

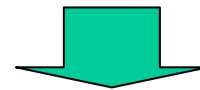
$$R = -\sqrt{3} \frac{\hbar^2}{2m_0} [\gamma_2 (k_x^2 - k_y^2) - 2i\gamma_3 k_x k_y] \approx -\sqrt{3} \frac{\hbar^2}{2m_0} \bar{\gamma} k_-^2$$

$$k_{\pm} = -ie^{\pm i\varphi} \left( \frac{\partial}{\partial r} \pm \frac{i}{r} \frac{\partial}{\partial \varphi} \right)$$

**Hamiltonien avec déformations :**

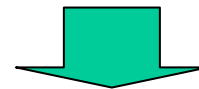
$$R_{\varepsilon} = \frac{b\sqrt{3}}{2} (\varepsilon_{rr} - \varepsilon_{\varphi\varphi}) \cos(2\varphi) - i \frac{d}{2} (\varepsilon_{rr} - \varepsilon_{\varphi\varphi}) \sin(2\varphi) \approx \frac{\bar{b}\sqrt{3}}{2} (\varepsilon_{rr} - \varepsilon_{\varphi\varphi}) e^{-i2\varphi}$$

*Even Phys. Rev. B 2008*



### Diagonalisation par blocs Fz de l'Hamiltonien :

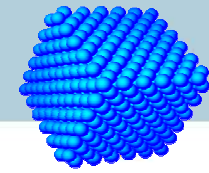
“Bon” nombre quantique : le moment angulaire total  $F_z = J_z + L_z$



Developpement de la fonction d'onde :  $|J, J_z\rangle |L_z = F_z - J_z\rangle$

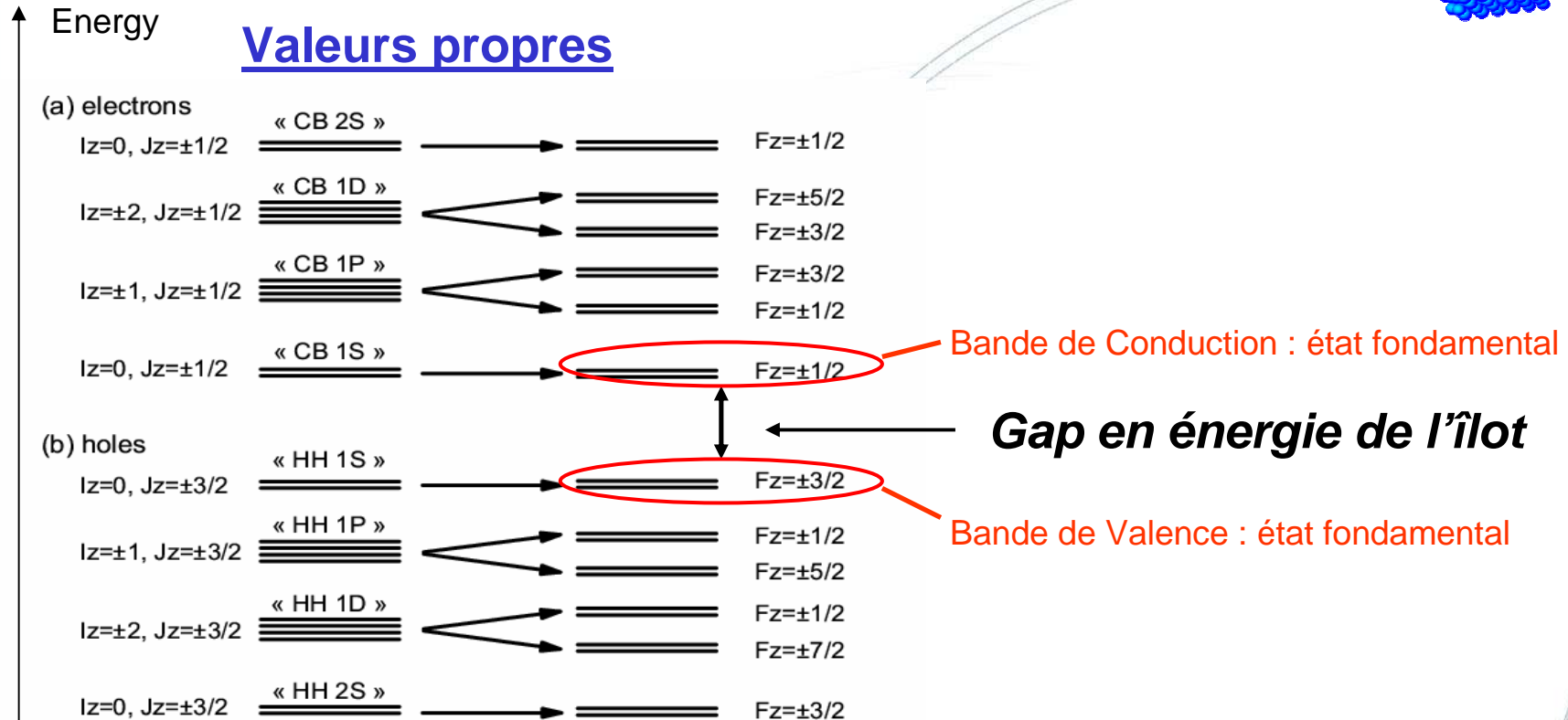
Base des 8 fonctions de Bloch du massif  $u_i$  ( $i=1\dots 8$ )

8 fonctions enveloppes de (r,z) correspondant aux RI de  $C_{\infty v}$



# Modèle k.p axial à 8 bandes

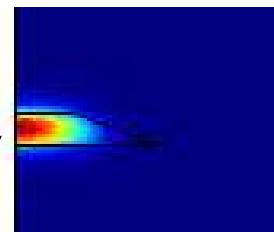
## Valeurs propres



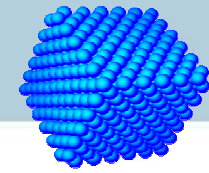
## Pour chaque valeur propre : 8 fonctions enveloppes

Exemple : BC état fondamental  $F_z = +1/2$

Condition : Neumann



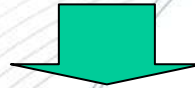
Type S  
BC (electron)  
 $u_2$  fonction enveloppe



## Modèle k.p axial à 8 bandes (femlab)

2 variables

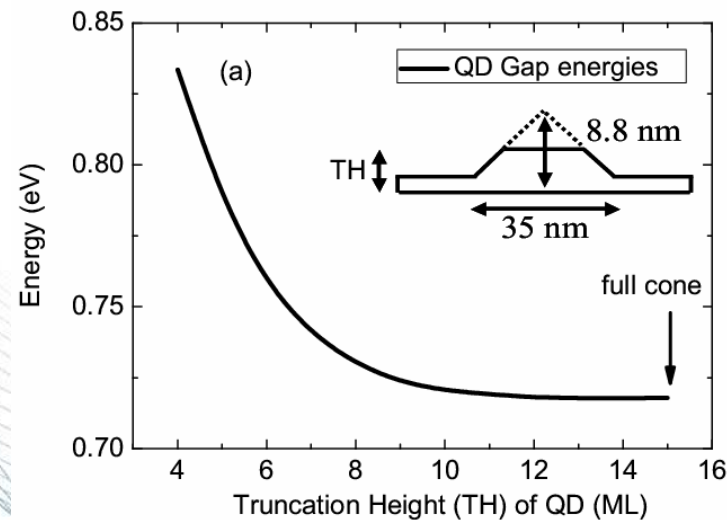
**Strains :**  
**Solver Manager - Solve For Axial Symmetry**  
**Solver Parameters : Stationary Linear**

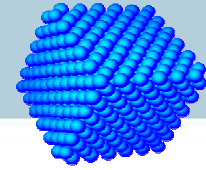


8 variables

**Hamiltonian : Ground state CB**  
**Options - Constants  $Fz = 1/2$**   
**Solver Manager - Solve For Coefficient form (c)**  
**Solver Manager : Initial Value Stored solution**  
**Solver Parameters : Eigenvalue 0.27**

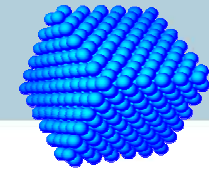
Exemple : variation du gap (InAs/InP)



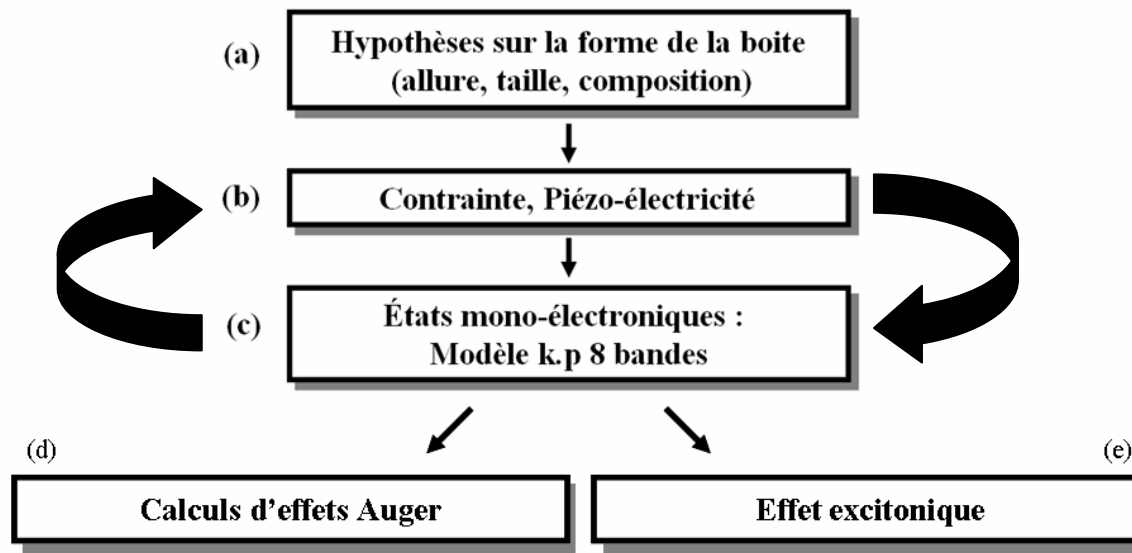


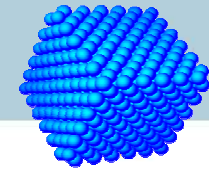
- I. Introduction
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## Applications : un “toolbox” extensible





# Application no1 : Perturbation piezoélectrique (femlab)

**Hamiltonian : Ground state CB**  
**Options - Constants**  $F_z = 1/2$   
**Solver Manager - Solve For** Coefficient form (c)  
**Solver Manager : Initial Value** Stored solution  
**Solver Parameters :** Eigenvalue 0.27

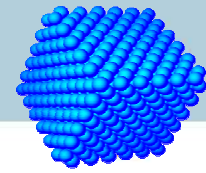
**Strains :**  
**Solver Manager - Solve For** Axial Symmetry  
**Solver Parameters :** Stationary Linear

**Poisson equation : piezoelectric potential**  
**Solver Manager - Solve For** Coefficient form (c)  
**Solver Manager : Initial Value** Stored solution  
**Solver Parameters :** Stationary Linear

matlab

	CB ground state	CB excited state
InAs/InP QD, without piezo $F_z =$ $+/- 1/2$	(a)	(b) $F_z =$ $+/- 1/2$

	CB first and second excited states	
InAs/InP QD, with piezo $F_z =$ $+/- 1/2$	(c)	(d)
InAs/GaAs QD, with piezo $F_z =$ $+/- 1/2$	(e)	(f)



## Application no2 : Perturbation excitonique (femlab)

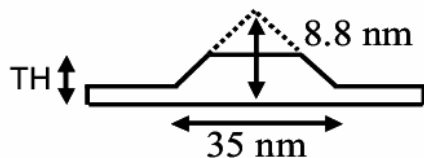
### Energie de liaison de l'exciton : interaction electron-trou

Approximation de Hartree et résolution auto-cohérente de l'équation de Poisson (O. Stier Phys. Rev. B59 (1999))

$$\begin{array}{ccc}
 [H + V_h] \Psi_e = \tilde{E}_e \Psi_e & \longleftarrow & e |\Psi_h|^2 = \epsilon_0 \nabla (\epsilon_s \nabla V_h) \\
 \text{CB Ground state} & & \text{VB Hartree potential} \\
 \downarrow & & \uparrow \\
 -e |\Psi_e|^2 = \epsilon_0 \nabla (\epsilon_s \nabla V_e) & \longrightarrow & [H + V_e] \Psi_h = \tilde{E}_h \Psi_h \\
 \text{CB Hartree potential} & & \text{VB Ground state}
 \end{array}$$

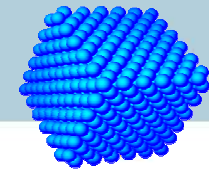
➔  $E_X = (E_e - E_h) - (\tilde{E}_e - \tilde{E}_h) - (\langle \Psi_h | V_e | \Psi_h \rangle - \langle \Psi_e | V_h | \Psi_e \rangle) / 2$

Exemple de calcul autocohérent dans Femlab : InAs/InP cone tronqué (TH=9ML)



sans confinement dielectrique ( $\epsilon_{\text{InAs}} = \epsilon_{\text{InP}}$ ) :  
 $E_X = 14 \text{ meV}$

avec confinement dielectrique ( $\epsilon_{\text{InAs}} \neq \epsilon_{\text{InP}}$ ) :  
 $E_X = 17 \text{ meV}$



# Application no2 : Perturbation excitonique (femlab)

**Strains :**  
**Solver Manager - Solve For** *Axial Symmetry*  
**Solver Parameters :** *Stationary Linear*

**Hamiltonian : CB Ground state**  
**Options - Constants** *Fz = 1/2*  
**Solver Manager - Solve For** *Coefficient form (c)*  
**Solver Manager :** *Initial Value Stored solution*  
**Solver Parameters :** *Eigenvalue 0.27*

**Poisson equation : VB Hartree potential Vh**  
**Solver Manager - Solve For** *Coefficient form (c4)*  
**Solver Manager :** *Initial Value Stored solution*  
**Solver Parameters :** *Stationary Linear*

*Matlab (+ Femlab) : 12 variables*

**Poisson equation : CB Hartree potential Ve**  
**Solver Manager - Solve For** *Coefficient form (c3)*  
**Solver Manager :** *Initial Value Stored solution*  
**Solver Parameters :** *Stationary Linear*

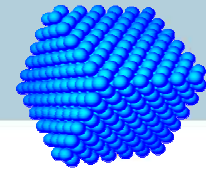
**Hamiltonian : VB Ground state**  
**Options - Constants** *Fz = 3/2*  
**Solver Manager - Solve For** *Coefficient form (c)*  
**Solver Manager :** *Initial Value Stored solution*  
**Solver Parameters :** *Eigenvalue - 0.45*

*Convergence (self-consistency): export*

**Matlab Integration :**  
 $\langle \Psi_h | V_e | \Psi_h \rangle$

**Matlab Integration :**  
 $\langle \Psi_e | V_h | \Psi_e \rangle$

**Exciton energy :**  
 $Ex = Ee' - Eh' + \langle \psi_{sie} | V_h | \psi_{sie} \rangle / 2 - \langle \psi_{sih} | V_e | \psi_{sih} \rangle / 2$



Exciton

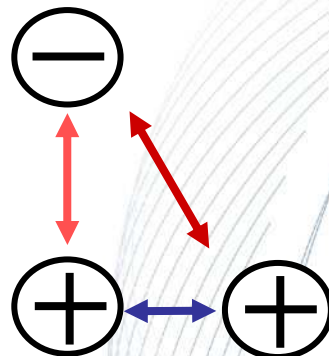
**X**



$$E_{bx} = 16.0 \text{ meV}$$

Trion Positif

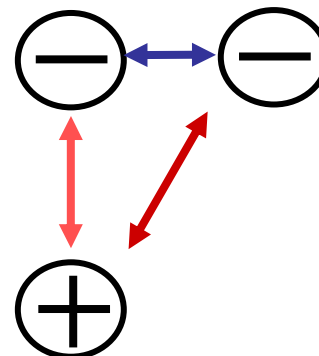
**X+**



$$E_{bx+} = 0.5 \text{ meV}$$

Trion Négatif

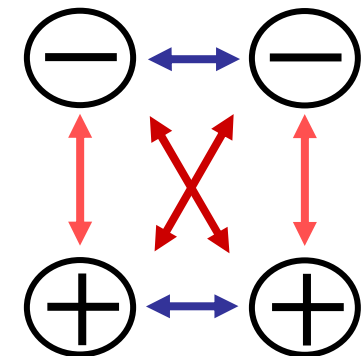
**X-**



$$E_{bx-} = 4.0 \text{ meV}$$

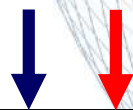
Biexciton

**XX**



$$E_{bxx} = 3.6 \text{ meV}$$

**X- XX**



**X+**

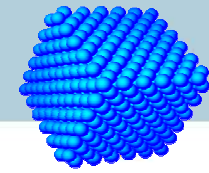


**X**

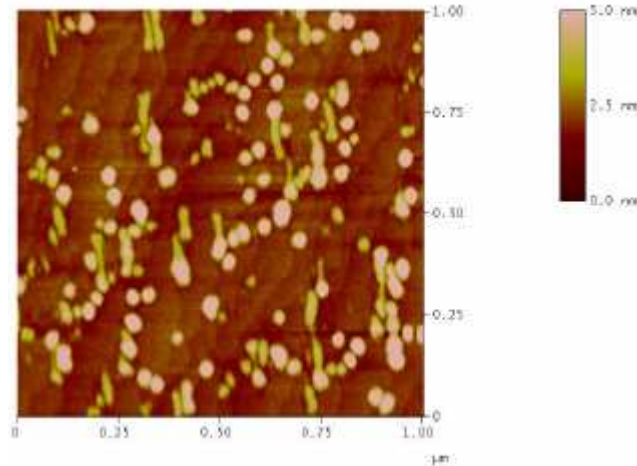


Energie d'émission

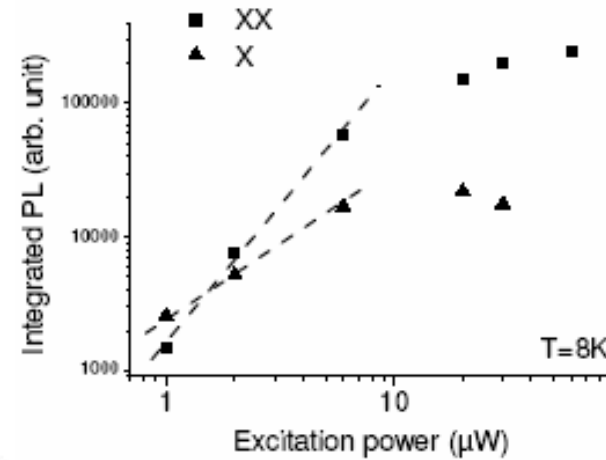
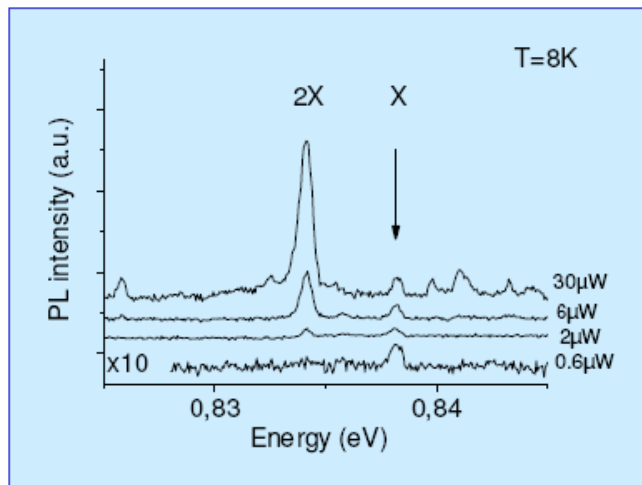




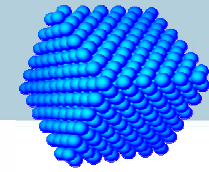
# Application no3 : Effets à n-corps multiexcitoniques



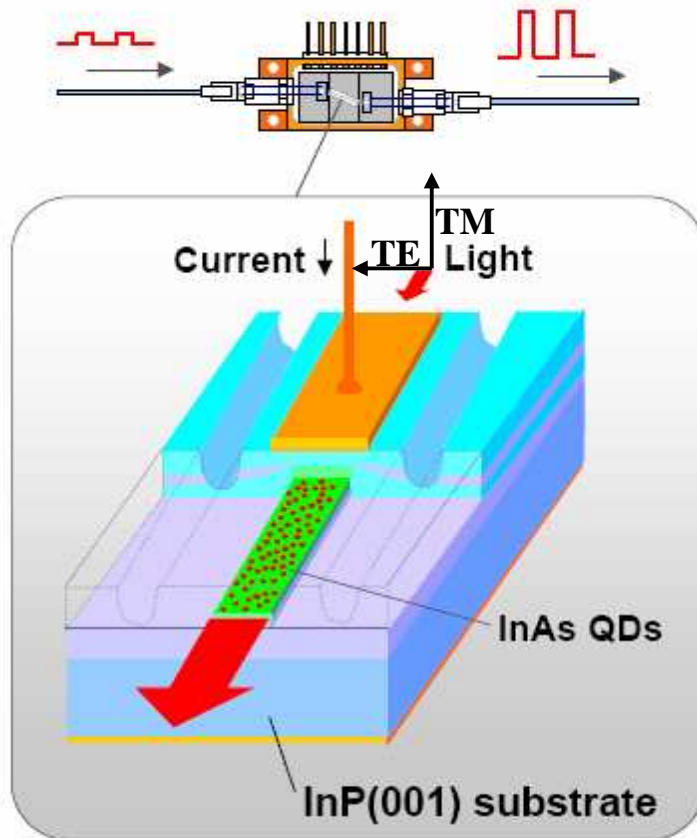
**Petits îlots**  
**Densité faible**  
**Emission à 1.55µm**  
**(N. Chauvin 2006)**



**Energie de liaison du biexciton ~5meV !!**

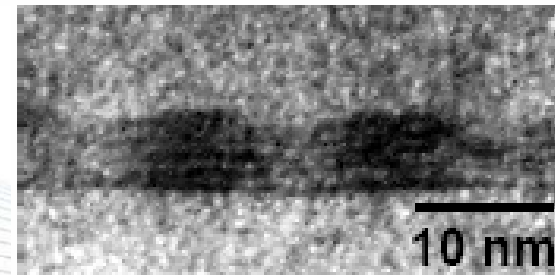
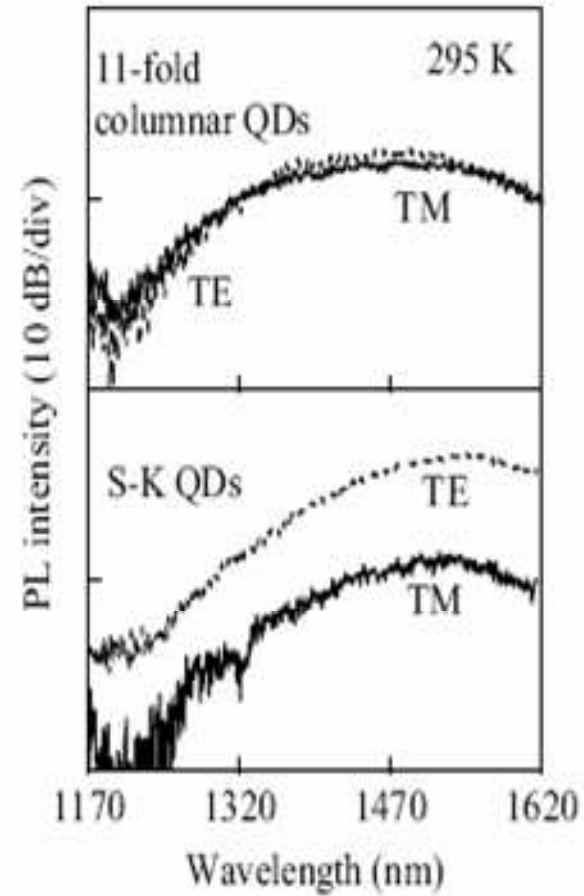


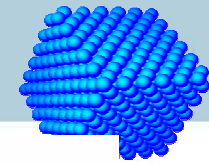
# Application no4 : Insensibilité à la polarisation



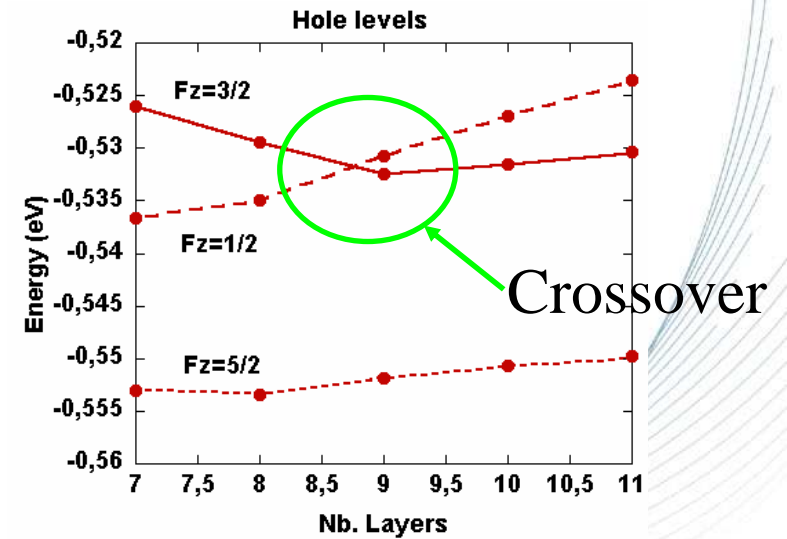
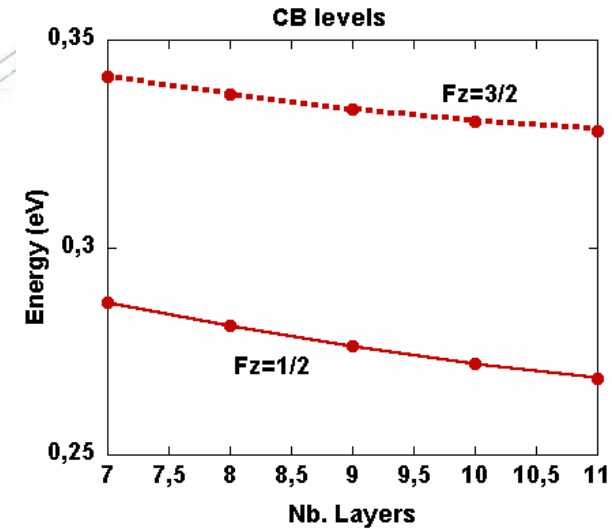
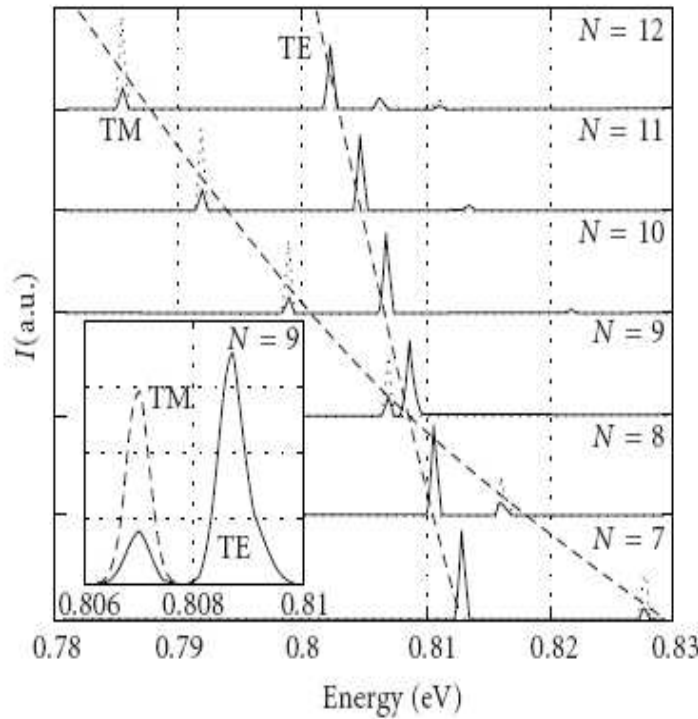
Kawagushi (Fujitsu, 2006)

## Amplificateurs optiques





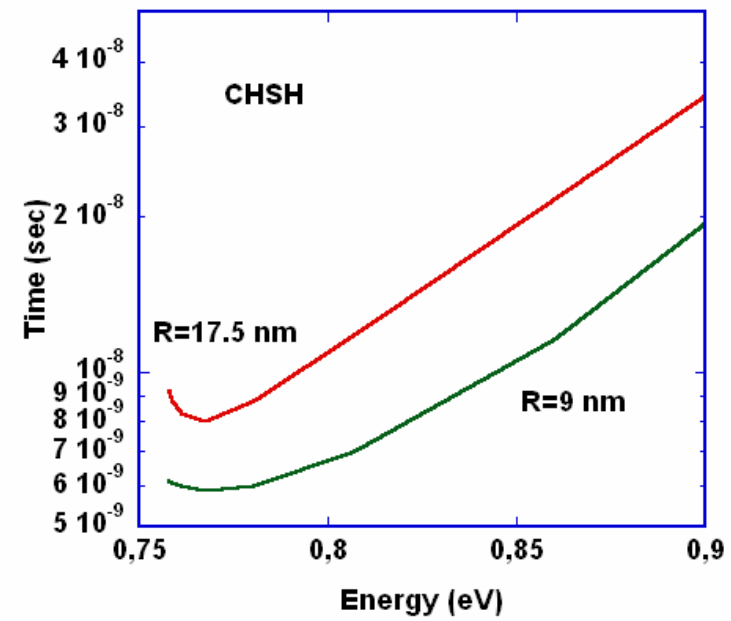
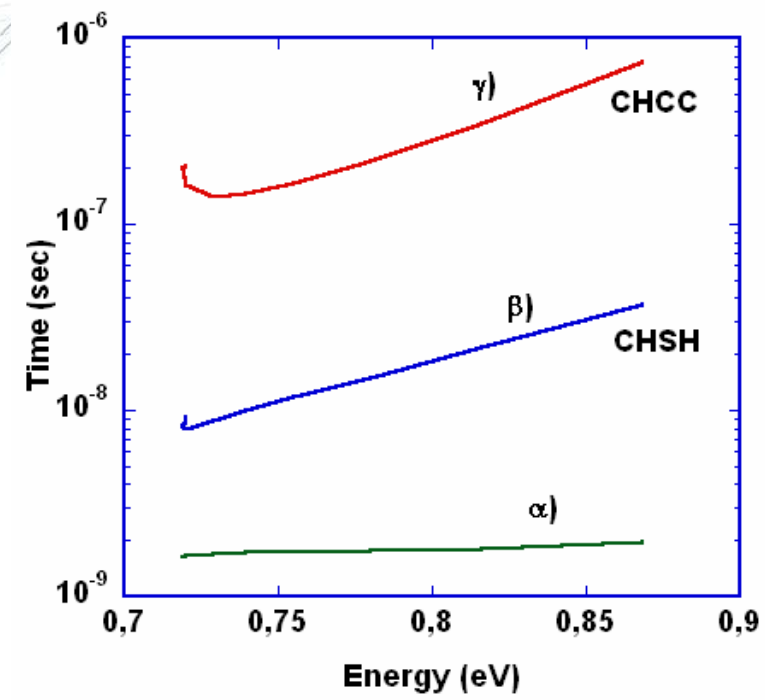
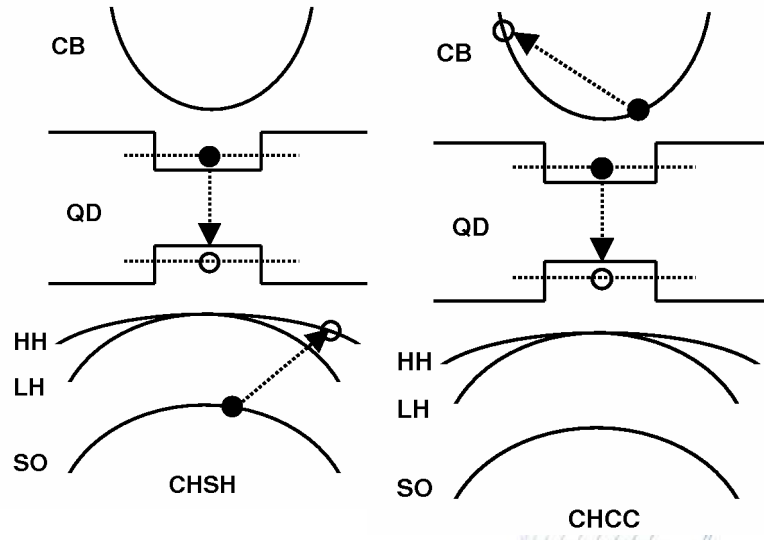
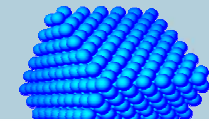
# Application no4 : Insensibilité à la polarisation

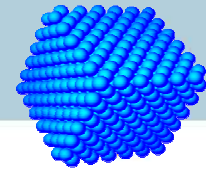


**Insensibilité à la polarisation  
d'îlots columnaires**



# Application no5 : Effet Auger dans les lasers à îlots





## Conclusion :

- Il existe d'autres applications (en dehors des telecoms)
- Il existe d'autres types de nanostructures
- Il existe d'autres classes de matériaux (wurtzite ...)
- Il existe d'autres méthodes de calcul (ab initio, liaisons fortes ...)